

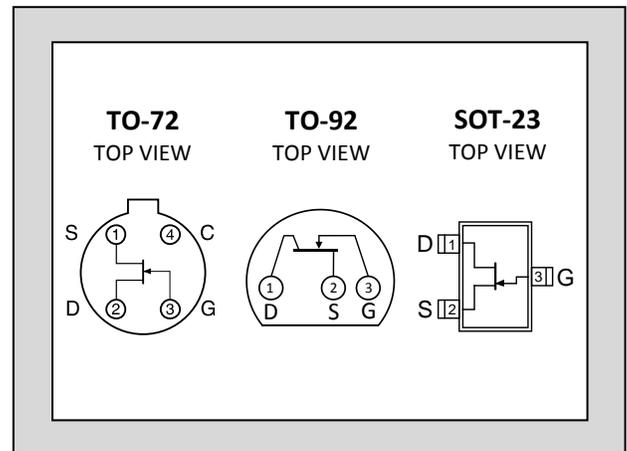
# LINEAR SYSTEMS

Over Three Decades of Quality Through Innovation

## LS846

LOW NOISE LOW LEAKAGE  
SINGLE N-CHANNEL  
JFET AMPLIFIER

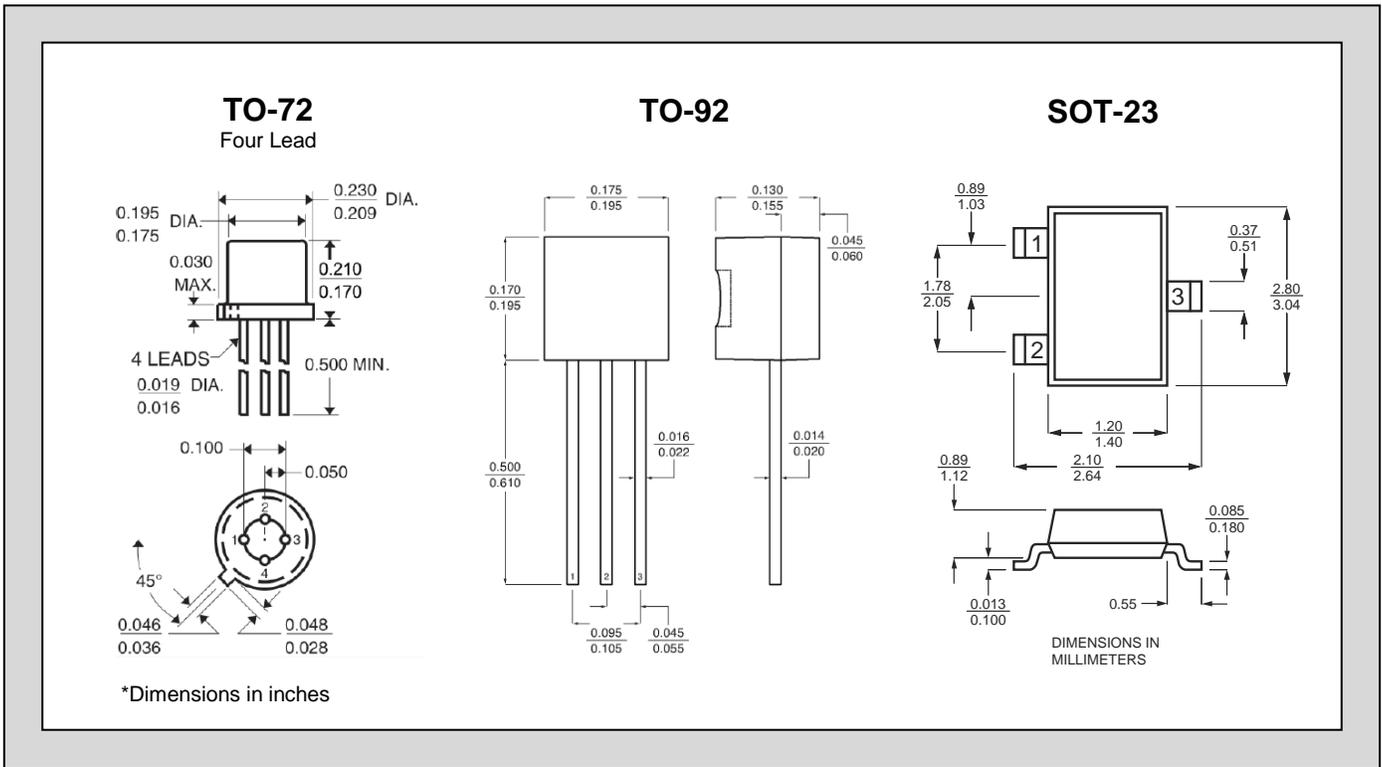
| FEATURES   |                       |
|--|-----------------------|
| ULTRA LOW NOISE  | $e_n = 3nV/\sqrt{Hz}$ |
| LOW INPUT CAPACITANCE  | $C_{iss} = 4pF$       |
| <b>ABSOLUTE MAXIMUM RATINGS<sup>1</sup></b><br>@ 25 °C (unless otherwise stated) |                       |
| <b>Maximum Temperatures</b>  |                       |
| Storage Temperature  | -55 to +150°C         |
| Operating Junction Temperature   | -55 to +150°C         |
| <b>Maximum Power Dissipation</b>   |                       |
| Continuous Power Dissipation TA=25°C   | 300mW <sup>3</sup>    |
| <b>Maximum Currents</b>  |                       |
| Gate Forward Current   | $I_{G(F)} = 10mA$     |
| <b>Maximum Voltages</b>  |                       |
| Gate to Source   | $V_{GSO} = 60V$       |
| Gate to Drain  | $V_{GDO} = 60V$       |



\*For equivalent Monolithic Dual, see LS843 Family

| SYMBOL        | CHARACTERISTIC <sup>2</sup>             | MIN  | TYP  | MAX  | UNITS          | CONDITIONS  |
|---------------|---|------|------|------|----------------|---|
| $BV_{GSS}$    | Gate to Source Breakdown Voltage        | -60  |      |      | V              | $V_{DS} = 0, I_D = 1nA$   |
| $V_{GS(OFF)}$ | Gate to Source Pinch-off Voltage        | -1   |      | -3.5 | V              | $V_{DS} = 15V, I_D = 1nA$   |
| $V_{GS}$      | Gate to Source Operating Voltage        | -0.5 |      | -3.5 | V              | $V_{DS} = 15V, I_D = 500\mu A$                                    |
| $I_{DSS}$     | Drain to Source Saturation Current      | 1.5  | 5    | 15   | mA             | $V_{DS} = 15V, V_{GS} = 0$  |
| $I_G$         | Gate Operating Current                  |      | -15  | -50  | pA             | $V_{DG} = 15V, I_D = 500\mu A$                                    |
| $I_G$         | Gate Operating Current Reduced $V_{DG}$ |      | -5   | -30  | pA             | $V_{DG} = 3V, I_D = 500\mu A$                                     |
| $I_{GSS}$     | Gate to Source Leakage Current          |      |      | -100 | pA             | $V_{GS} = 15V, V_{DS} = 0$  |
| $G_{iss}$     | Full Conductance Transconductance       | 1500 |      |      | $\mu S$        | $V_{DS} = 15V, V_{GS} = 0, f = 1kHz$                              |
| $G_{is}$      | Typical Operation Transconductance      | 1000 | 1500 |      | $\mu S$        | $V_{DS} = 15V, I_D = 200\mu A$                                    |
| $G_{OSS}$     | Full Output Conductance                 |      |      | 40   | $\mu S$        | $V_{DS} = 15V, V_{GS} = 0$  |
| $G_{OS}$      | Typical Operation Output Conductance    |      | 2.0  | 2.70 | $\mu S$        | $V_{DS} = 15V, I_D = 200\mu A$                                    |
| NF            | Noise Figure                            |      |      | 0.5  | dB             | $V_{DS} = 15V, V_{GS} = 0, R_G = 10M\Omega, f = 100Hz, NBW = 6Hz$ |
| $e_n$         | Noise Voltage                           |      | 3    | 7    | $nV/\sqrt{Hz}$ | $V_{DS} = 15V, I_D = 500\mu A, f = 1kHz, NBW = 1Hz$               |
| $e_n$         | Noise Voltage                           |      |      | 11   | $nV/\sqrt{Hz}$ | $V_{DS} = 15V, I_D = 500\mu A, f = 10Hz, NBW = 1Hz$               |
| $C_{iss}$     | Common Source Input Capacitance         |      | 4    | 8    | pF             | $V_{DS} = 15V, I_D = 500\mu A, f = 1MHz$                          |
| $C_{RSS}$     | Common Source Reverse Transfer Cap.     |      |      | 3    | pF             |   |

**STANDARD PACKAGE DIMENSIONS:**



**NOTES:**

1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
2. All MIN/TYP/MAX limits are absolute numbers. Negative signs indicate negative electrical polarity only.
3. Derate 2.8mW/°C above 25°C.

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